Electron diffraction and high-resolution transmission electron microscopy of the high temperature crystal structures of GexSb2Te3+x (x=1,2,3) phase change material
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I. INTRODUCTION

In recent years thin films composed of Ge$_2$Sb$_2$Te$_5$ have received increasing scientific attention because of their current use in optical recording as rewriteable memory media.\(^1\)\(^-\)\(^8\) Amorphous spots in a crystalline surrounding act as bits of information. Both continuous laser light and short laser pulses at various higher power densities can be employed to read, write, and/or erase those local amorphous areas and thus the phase changes in the material are exploited. The attractiveness of Ge$_2$Sb$_2$Te$_5$ originates from its clear optical contrast and its excellent reversibility between the amorphous and crystalline state, its high thermal stability at room temperature, and the high crystallization rates.\(^8\) Particularly, this latter feature is becoming increasingly important because of increasing demands on the rates of data transfer. Crystallization is considered the rate-limiting process, because amorphization is inherently a much faster process.\(^5\)\(^,\)\(^6\) It has been argued that a possible disadvantage of the use of Ge$_2$Sb$_2$Te$_5$ is that the crystalline state used in phase change optical recording applications is metastable,\(^10\)\(^,\)\(^11\) whereupon after an increased heat input (to higher temperatures) a stable structure develops. On the other hand, the demanded high crystallization rate of Ge$_2$Sb$_2$Te$_5$ is possibly a direct consequence of the metastability of the phase, which allows for a much easier crystallization process due to fewer constraints on the short range diffusion and ordering of the different atomic species. A precise knowledge of the structures of the metastable and stable crystalline phases is considered to be of importance in arriving at a complete understanding of the driving forces for crystallization. Recently, several papers have dealt with the structure of the metastable phase.\(^7\)\(^,\)\(^8\) In contrast, on the high temperature stable crystal structure of Ge$_2$Sb$_2$Te$_5$ only a single relatively older report exists.\(^12\) The purpose of the present work is to verify the correctness of the proposed stable crystal structure. Furthermore, rapid cooling rates have been used to solidify bulk Ge$_2$Sb$_2$Te$_5$ from the melt in order to obtain insight into how the structure responds to this phase transition starting from an amorphous phase. This is in contrast to the amorphous–crystalline transition at low temperatures that is exploited in phase change optical recording.

II. CRYSTAL STRUCTURES

Stable binary crystal structures in the Ge–Sb–Te system involve the phase GeTe (with a low and high temperature modification, both show a composition range with a width of about 1 at. %) and the rather stoichiometric phase Sb$_2$Te$_3$.\(^13\) Ge and Sb turn out to be immiscible in the solid state.\(^13\) GeTe at low temperature (<400°C) has a trigonal (R-3m) structure with a rhombohedral lattice constant of 0.5996 nm and \(\alpha=88.18^\circ\).\(^14\)\(^,\)\(^15\) At higher temperature it transforms to the NaCl (B1) type structure with a lattice constant of 0.60 nm (and most importantly \(\alpha\) changes to 90°). Sb$_2$Te$_3$ possesses also a trigonal \(R\cdot3m\) (tetradydite) structure with \(a=1.0426\) nm and \(\alpha=23^\circ31^\prime.\)\(^16\) Using hexagonal axes GeTe has \(a'=0.417\) and \(c'=1.071\) nm with an \(a,b,c\) stacking sequence of close packed planes along the \(c'\)-axis of Te–Ge–Te–Ge–Te–Ge– (i.e., the close packed planes consist of the atoms of only one element). The high temperature GeTe structure can also be considered in this way, but then \(a'\) is 0.424 nm. In Sb$_2$Te$_3$ the lattice parameters are \(a'=0.425\) and \(c'=3.04\) nm with an \(a,b,c\) stacking along the \(c'\)-axis of Te–
Sb–Te–Te–Sb– (three times repeated, because the $a',b',c'$ stacking requires that the number of planes along the $c'$-axis within the unit cell is always a multiple of 3).

This rather extensive information is intriguing when considering the metastable and stable crystalline structures of Ge$_2$Sb$_2$Te$_5$. If we consider the stable structure, taking the sublattice proposed in Ref. 17 for GeSb$_2$Te$_4$ and in Ref. 12 for Ge$_3$Sb$_2$Te$_6$, it is reported that $a'=0.420$ and $c'=1.696$ nm and the space group is primitive rhombohedral ($P-3m1$). However, the stacking sequence was derived as Te–Ge–Te–Sb–Te–Te–Ge– and a trigonal cell with hexagonal axes with dimensions $a'=0.42$, $c'=1.72$ nm. Here, the cell is now primitive because the number of layers is nine, which is directly a multiple of three. Indeed, for Ge$_2$Sb$_2$Te$_5$, it is reported that $a'=0.420$ and $c'=1.696$ nm and the space group is primitive rhombohedral ($P-3m1$). However, the stacking sequence was derived as Te–Ge–Te–Sb–Te–Te–Ge– and a trigonal cell with hexagonal axes with dimensions $a'=0.42$, $c'=1.72$ nm. Here, the cell is now primitive because the number of layers is nine, which is directly a multiple of three. Indeed, for Ge$_2$Sb$_2$Te$_5$, it is reported that $a'=0.420$ and $c'=1.696$ nm and the space group is primitive rhombohedral ($P-3m1$).

The metastable crystalline phase of Ge$_2$Sb$_2$Te$_5$ turns out to have the NaCl-type structure, with the Te atoms on one fcc sublattice (e.g., Cl sites) and with the Ge and Sb atoms and (thus) 20% of vacancies distributed randomly over the other fcc sublattice. The lattice constant, depending on the exact composition and temperature, is $a=0.60$ nm. This structure is thus almost identical to the one of binary GeTe. In this sense it is remarkable that Ge and Sb want to occupy the same close-packed plane. The repulsion between Ge and Sb can be counteracted by the neighboring Te planes, and possibly the vacancies are essential for stabilizing the structure. Nonetheless it is not remarkable that this structure is metastable.

Based on the GeTe and Sb$_2$Te$_3$ (and Ge–Sb) binary structures it may be expected that, in general, the phases Ge$_x$Sb$_{2-x}$Te$_3$ (with $x$ an integer) consist of an alternation in $c'$-direction of one repeat unit of Sb$_2$Te$_3$ and a block consisting of $2x$ layers GeTe. The purpose of this article is to show that this picture holds and that the stacking sequences proposed in Ref. 17 for GeSb$_2$Te$_4$ and in Ref. 12 for Ge$_2$Sb$_2$Te$_5$ are erroneous. Furthermore, the structure of Ge$_2$Sb$_2$Te$_5$ will be assessed using electron diffraction and high-resolution transmission electron microscopy (HRTEM). The structure proposed in Ref. 12 for Ge$_2$Sb$_2$Te$_5$ is in agreement with the present picture, because the unit cell in the $c'$-direction consists of two repeat units of Sb$_2$Te$_3$ separated by a 2 layer GeTe block.

Perfect crystals are not likely in practice and stacking disorder is likely to occur in the Ge–Sb–Te system. For instance, Ge$_2$Sb$_2$Te$_5$ crystals may show local GeSb$_2$Te$_4$ stacking that has to be compensated by the local presence of Ge$_2$Sb$_2$Te$_6$. From equilibrium, many possible stacking sequences with GeTe double layers and Sb$_2$Te$_3$ repeat units may be possible as long as the overall composition is finally attained.

III. EXPERIMENTAL PROCEDURES

Ge$_2$Sb$_2$Te$_5$ alloys were produced by mixing the pure components (Ge:6 N, Sb and Te both 5 N) in an evacuated quartz tube at 750°C. The melt was solidified using three different cooling rates: (i) furnace cooled, (ii) pulled out of the furnace on a metal plate at room temperature, and (iii) quenching the liquid material into water (dispersing the melt into small solid pieces). Pieces of the alloy according to (i) and (ii) were also annealed 24 h at 400°C. TEM samples were prepared by grinding, dimpling, and ion milling (using a Gatan PIPS at 4 kV with Ar sputtering from ±6°) 3 mm discs to electron transparency. Small pieces of the water-quenched sample were ground to a fine powder in a mortar and dispersed in isopropanol. A droplet of the suspension was put on a Si-nitride membrane and dried before insertion in the TEM. The selected area electron diffraction patterns and HRTEM images were obtained using a JEOL 4000 EX/II operating at 400 kV and energy dispersive x-ray spectra were recorded using a JEOL 2010F operating at 200 kV equipped with an EDAX detector containing a so-called “super-ultra” thin window.

IV. RESULTS

Selected-area electron diffraction (SAED) patterns originating from three different grains in the same TEM sample of Ge$_2$Sb$_2$Te$_5$ that was cooled relatively fast from the melt are presented in Fig. 1. Here, the quartz tube was pulled out...
of the furnace on a metal plate at room temperature. Analysis of the central pattern indicates a d-spacing corresponding to the row of finely spaced reflections of 1.727 nm and orthogonal to this a e-spacing of 0.368 nm. Because no pattern with more densely spaced reflections in these two orthogonal directions could be found, the 1.727 and 0.368 nm values correspond to the lowest index reflections possible. On the basis of the intensity modulation of the reflections, that is, a period of 9 along the row with finely spaced reflections and a period of 3 perpendicular to that, and because no systematic absences were found (along the line with a multiple of 3, reflections are present on each finely spaced row), a primitive trigonal unit cell with \( a'/=0.425 \) and \( c'/=1.727 \) nm with nine layers according to the \( a',b',c' \) stacking along the \( c' \)-axis is found to hold for the crystal. These results agree with the in all three SAED patterns and denotes an amount of disorder. Ge\(_3\)Sb\(_2\)Te\(_6\) may be unstable but as long as GeSb\(_2\)Te\(_4\) is present it cannot disappear due to the constraint of the overall composition.

The degree of stacking disorder can easily be observed in conventional TEM images. Figure 2 presents an example for a Ge\(_3\)Sb\(_2\)Te\(_6\) grain in which the typical stacking fault contrast can be observed from inclined basal planes in the TEM foil. Still, a lamella with a thickness of about 300 nm is present in which no stacking faults occur. Also some dislocation contrast can be recognized in Fig. 2.

As a matter of course, it is questionable whether the analysis of crystal structures for relatively quickly cooled samples yields the crystal structure of stable crystals. However, after annealing a slowly furnace cooled alloy 24 h at 400 °C, identical diffraction patterns were observed. Trying to quench the melt more rapidly by breaking a quartz tube with the molten alloy in water (dispersing the alloy into small solid pieces) also showed the same crystal structures present. The fraction of stacking defects, that is, the amount of streaking, varies as a consequence of these different conditions, but the basic underlying structures remain intact.

In Ref. 12 the proposed stacking sequence for Ge\(_3\)Sb\(_2\)Te\(_6\) along the \( c' \)-axis is Te–Sb–Te–Ge–Te–Te–Te–Sb–Te–Sb–. Knowing the GeTe and Sb\(_2\)Te\(_3\) crystal structures this sequence is an anomaly and a more logical structure is Te–Ge–Te–Sb–Te–Te–Sb–Te–Ge–, that is, Ge and Sb exchange positions. Simulation of the diffraction patterns for these two sequences, using full dynamical diffraction (MacTempas\(^{10}\)), were carried out, keeping all other parameters fixed, for example, convergence angle 0.2 mrad and crystal thickness 7 nm. The resulting patterns are shown in Fig. 3; the top one is based on the anomalous sequence of Ref. 12 (“Old”) and the bottom one is the sequence proposed here (“New”). The intensity of the reflections is deliberately low in order to make the variations in intensity more distinct. For this reason some reflections may disap-
pear, but are in fact not really absent. A comparison between
the two simulated patterns in Fig. 3 with the central pattern
in Fig. 1 makes clear that the new sequence matches the
experimental results better than the old one. It should be
realized that there is no need to perform an elaborate fitting
procedure. Of course, both satisfy the intensity modulation
with a period of 9 along the $c'$-axis and a period of 3 along
the $a'$-axis. However, one of the clear differences is that the
sub-period intensity modulation in the period of 9, with one
additional maximum for the 0004 and 0005 reflection indi-
cated by an arrow in the central pattern of Fig. 1 is repro-
duced well in the bottom pattern of Fig. 1 and not in the top
pattern, where two additional maxima occur.

So far, no previous reports on the crystal structure of
Ge$_3$Sb$_2$Te$_6$ have been found. Figure 4 presents a simulation
of its diffraction pattern for the [11-20] zone axis (lattice
constants $a' = 0.425$ nm, $c' = 6.252$ nm, space group $R-3m$
with the $a,b,c$ stacking sequence proposed above, conver-
gence angle of 0.2 mrad, crystal thickness 10 nm). Of course,
 apart from streaking, this simulated diffraction pattern repro-
duces excellently the experimental one on the right in Fig. 1.

In order to verify the stacking sequence, atomic scale
HRTEM images were recorded. In Fig. 5 a HRTEM image of
a 'Ge$_3$Sb$_2$Te$_6$' crystal is presented with a simulated image
as inset (middle left). The simulation parameters were: 400
kV, $C_s$: 1 mm, convergence angle:1 mrad, spread in defocus:
10 nm, defocus: $-10$ nm, thickness: 6 nm. Because Sb and
Te are heavy elements that are neighbors in the periodic
table; their scattering factors are almost identical and there-
fore dark or bright spots on the position of the atomic col-
umns of Sb or Te are also nearly identical. Thus, deviating
contrast in the layered structure stems from the close packed
Ge planes. This simple reasoning is confirmed by the image
simulations performed for different defocus values of the mi-
croscope and different thicknesses of the samples. Ideas for a
direct structure reconstruction, that is, solving the inverse
problem$^{19,20}$ are based on the channeling effect, where the
electrons of the incoming wave remain highly localized on
the atomic columns, and the exit wave thus directly repre-
sents the projected structure, also reflecting the chemical
content of the columns. In the HRTEM image in Fig. 5 it can
be seen that each time a block of small dots (Sb and Te
atoms) are separated by three rows containing elongated
black dots. These three rows with deviating intensity correspond to the three Ge–Te double layers present in the Ge₃Sb₂Te₆ structure. Hence, on an atomic level the structure proposed on the basis of electron diffraction is also confirmed. The length of the c’-axis of somewhat more than 6 nm can also be derived on the basis of the HRTEM image as indicated by the dashed line in the center of the image; if we start at say an a position, then after what seems one repeat unit we are on a c position, after two repeat units on a b position, and only after the third unit we are back at the a position.

Stacking disorder can be observed in Fig. 5 because all repeat units along the c’-axis have the same thickness corresponding to the 11 layers of Ge₃Sb₂Te₆, but the two neighboring blocks have a thickness that is about 18% larger than the repeat unit (c’/3) of Ge₃Sb₂Te₆ (as indicated in Fig. 5). Therefore, the additional thickness is about 0.38 nm, which agrees well with the thickness of the Sb–Te–double layer (see above). In addition, the contrast in the HRTEM image associated with the additional thickness agrees with the one that would originate from the Sb₂Te₃ block.

Figure 6(a) presents another HRTEM image of this ‘‘Ge₃Sb₂Te₆’’ crystal with a different defocus and a different thickness than in Fig. 5. In the image the bright dots are on the atomic columns. Because we know that each atomic plane having its normal parallel to the c’-axis contains in principle only the atoms of a single element, it is logical to average the intensities in the image along the atomic planes and to transform the image into a line profile. The resulting line profile is also shown in Fig. 6(a). We may try to match the maximum in intensities to the atomic species. Because it is clear from the image simulations that the largest deviations in intensity originate from the Ge planes, we can more or less judge their positions, that is, peaks with highest maximum. In between these regions with the bright Ge peaks in the line profile, two neighboring peaks with the same lowest intensity are present. Because we know that in between the Ge–Te double layers an Sb₂Te₃ block with a central Te–Te double layer is present, these neighboring peaks with the same low intensity can be ascribed to this Te–Te double layer. On both sides of this double layer Sb should be present, and apparently the Sb gives peaks with slightly higher intensity than Te, but clearly lower than Ge. These central blocks of Sb–Te–Te–Sb– when clearly observable...
are indicated in the line profile by \( \times^a_T \). The line profile thus seems to clearly reflect the different chemical species in the individual layers. The average of five periods in the line profile, which appear identical in Fig. 6(a), is presented in Fig. 6(b), showing the basic repeat unit in the GeSb2Te6 structure with the chemical interpretation of each maximum indicated. Clearly, the expected structure for the repeat unit in GeSb2Te6 is reproduced. One plane having intermediate intensity between the ones ascribed to pure Ge and Sb planes is denoted as a plane containing both Ge and Sb atoms. In view of the known metastable NaCl-type structure of GeSb2Te5, where Te occupies the Cl sites and Ge and Sb and 20% vacancies mix randomly on the Na sites, it may not be surprising that what in the above results are consistently called pure Ge or Sb planes may in fact be impurified with atoms of the other element. However, because this will make the discussion more complicated and because it is very hard to supply direct evidence for the presence of Sb on the Ge planes and vice versa, this mixing effect can not receive serious attention in this article. In addition, errors will be made when intensities in the line profile are directly linked to the chemical composition. This procedure and the results are only within certain precautions correct for (the phase image of) the exit wave if the distance between the atomic columns is not too small\(^{19,20}\) and are not correct for an image where the transfer function of the microscope comes into play. For instance, residual beam tilt (always present to some extent in the image because a voltage center and not a comma-free alignment is performed) will lead for instance to differences in intensity for the “a” and “b” stacked planes in simple close-packed hexagonal structures even if the chemical composition of both plane types is identical.\(^{21}\) Thus, the intensities in the line profile of Fig. 6 are a complicated interplay of structural and imaging parameters and can in principle not be interpreted intuitively. For instance, the different intensities of what are interpreted as the Ge planes in the line-profile Fig. 6(b) can be largely influenced by beam tilt. Nevertheless, although the interpretation in Fig. 6(b) with the denoted chemical elements is tentative, it remains nicely in accordance with the expectation for GeSb2Te6.

V. DISCUSSION

Quenching liquid GeSb2Te5 in water did not result in a solid amorphous structure. The metastable phase of GeSb2Te3, that is, the NaCl-type structure with Te occupying one fcc sublatticed (e.g., the Cl sites) and Ge and Sb and 20% vacancies randomly mixed on the other sublattice (Na sites), was also not observed. However, clear deviations from the stable GeSb2Te3 structure, that is, trigonal with a primitive hexagonal cell with Te–Ge–Te–Sb–Te–Sb–Te–Sb–Te–Ge– stacking along the c’-axis, do occur upon quenching. Two other dominating structures corresponding to stoichiometries of GeSb2Te4 and GeSb3Te6 were also observed. It is clear that nuclei of these three different phases form in the same melt and can grow simultaneously. Within each crystal, disorder in stacking sequences is present. Higher cooling rates probably imply a larger fraction of GeSb2Te4 and GeSb3Te6 crystals and certainly imply more faults in stacking order. Basic units in all the crystals, including those with a large fraction of disorder, are Ge–Te double layers, also present in binary GeTe, and Te–Sb–Te–Sb–Te–Sb– and Sb–Te double layers, also present in binary Sb2Te3. It may be that all possible stable crystal structures in the ternary Ge–Sb–Te system will be built out of these basic units and will have \( a, b, c \) stacking. A decrease of stability will first increase the stacking disorder and will subsequently increase the amount of intermixing of the atoms in the Sb and Ge planes. Finally, a metastable phase with \( a, b, c \) stacking develops that is now known as the crystalline phase that is exploited in GeSb2Te3 phase change material.

Despite the strong resemblance between the structures of the melt and the solid amorphous phase employed in phase change optical recording, the characteristics of crystallization from the melt versus an amorphous solid are largely different. Dominant differences are the larger amount of latent heat released during the transition from liquid to solid, and the much faster diffusion during crystallization from the melt than from the solid amorphous phase. Diffusion rates are different not only due to the difference in temperature, but also because of diffusion in the melt versus the solid state. Therefore, formation of the metastable phase from the melt is less likely to occur.

Starting from a homogeneous amorphous state of GeSb2Te3 the metastable GeSb2Te3 structure requires much less dedicated diffusion and ordering than the stable one and the crystallization rate (i.e., growth rate) can thus be higher. In Refs. 5 and 6 it is in principle shown that the growth rate of the metastable crystalline phase depends on the “embryos.” The crystallization proceeds in 10 ns in case of Ref. 6 where embryos are already present, whereas the crystallization time increases to 100 ns if embryos are absent. This suggests that arguments based on the amorphous/crystalline interfacial energy \( \gamma \) are more important than arguments based on diffusion and ordering. The interfacial energy together with the strain energy involved determines the critical size \( r^* \) of a stable crystalline nucleus in the amorphous matrix and the activation energy \( \Delta G^* \) to arrive at this size.\(^{22}\) For a spherical nucleus it holds:\(^{22}\)

\[
\frac{2 \gamma}{(\Delta G_v - \Delta G_s)}
\]

\[
\Delta G^* = \frac{16 \pi \gamma^3}{3(\Delta G_v - \Delta G_s)^2}
\]

where \( \Delta G_s \) is the strain energy in the nucleus and surrounding matrix introduced per unit volume of the nucleus, and \( \Delta G_v \) is the difference in Gibbs-free energy per unit of volume of bulk between the phase in the matrix and the one that develops in the nucleus. The last term is the driving force, while the other term opposes the transformation. It is fairly safe to state that both the interfacial energy and the strain energy corresponding to a nucleus with the NaCl-type structure is clearly lower than for the rhombohedral structure with its larger c’-axis. The NaCl structure more closely resembles the surrounding amorphous state. Therefore, although the driving force \( \Delta G_v \) for crystallization in the metastable structure is definitely lower, this is easily outweighed by the
lower interfacial and strain energy. Note that in the activation energy the interfacial energy $\gamma$ goes to the power of 3 whereas the driving force $\Delta G_V$ goes to the power of 2. Since it is now well-proven that in phase change optical recording Ge–Sb–Te shows growth-limited (i.e., nucleation-driven) crystallization as opposed to for instance, Ag–In–Sb–Te that shows nucleation-limited crystallization,$^9$ it is particularly clear that nuclei form very easily in Ge–Sb–Te. This is fully consistent with the physical picture presented here based on the difference in stable and metastable crystal structures.

VI. CONCLUSIONS

The crystal structures of Ge$_x$Sb$_2$Te$_{3+x}$ ($x = 1, 2, 3$) phase change material have been determined based on electron diffraction and HRTEM. Ge$_2$Sb$_2$Te$_5$ can be described as having a trigonal structure with a primitive hexagonal unit cell (e.g., space group $P-3m1$) with $a' = 0.425 \text{ nm}$ and $c' = 1.827 \text{ nm}$, and with a stacking sequence of pure Te–Ge–Te–Sb–Te–Te–Sb double layer both also present in binary GeTe and a Te–Sb–Te–Te–Sb–Te–Sb repeat unit larger fraction of disorder, are a Ge–Te double layer also present in binary Sb–Te basal planes along the $c'$-axis of the unit cell. This basic repeat unit contains one Ge–Te double layer in GeSb$_2$Te$_4$ and one more in Ge$_2$Sb$_2$Te$_6$. Because the unit cell requires a $c'$-axis with 3$n$ basal planes, both GeSb$_2$Te$_4$ and Ge$_2$Sb$_2$Te$_6$ contain three such basic repeat units per unit cell. Thus, the lattice parameters of GeSb$_2$Te$_4$ and Ge$_2$Sb$_2$Te$_6$ are $a' = 0.425$, $c' = 4.10$ nm and $a' = 0.425$, $c' = 6.26$ nm, respectively, and in both cases the space group is $R-3m$. The stacking sequence proposed here for GeSb$_2$Te$_4$ and Ge$_2$Sb$_2$Te$_6$ differs from the ones proposed earlier and no previous report on Ge$_2$Sb$_2$Te$_6$ apparently exists.

The Ge$_x$Sb$_2$Te$_{3+x}$ crystals were grown from molten Ge$_2$Sb$_2$Te$_5$, and higher cooling rates probably imply a larger fraction of GeSb$_2$Te$_4$ and Ge$_2$Sb$_2$Te$_6$ crystals and certainly imply a larger amount of stacking disorder of close-packed planes in the crystals. Basic units in all the crystals, also with larger fraction of disorder, are a Ge–Te double layer also present in binary GeTe and a Te–Sb–Te–Te–Sb–Te– repeat unit and a Sb–Te double layer both also present in binary Sb$_2$Te$_3$. It may be that all possible stable crystal structures in the ternary Ge–Sb–Te system will be built out of these basic units and will have $a, b, c$ stacking of the close-packed planes.

The fast crystallization rate from solid amorphous Ge$_2$Sb$_2$Te$_5$ to the metastable NaCl-type crystal structure can be understood, because the interfacial and strain energy associated with a nucleus with the metastable NaCl-type crystal structure is lower than with the complex stable trigonal structure (i.e., nucleation argument) and also because the former structure requires much less dedicated diffusion and ordering (i.e., growth argument).

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